

Recombination and Lifetimes of Charge Carriers in Semiconductors

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Abstract

In this Communication, it is shown that models used for describing generation and recombination of electrons and holes lead to disagreements with Maxwell's electrodynamics. Self-consistent expressions, more adequately depicting the actual physical processes of electron-hole recombination in semiconductors are obtained. It is shown that the electron and hole lifetimes can be defined correctly only for the special cases when the electron and hole nonequilibrium concentrations are the same, these lifetimes being equal. The influence of temperature inhomogeneity on the recombination is also considered. The recombination rate for hot electrons is obtained in the case when the electron and hole temperatures differ.

Generation and recombination phenomena involving electron and holes are very important processes in any nonequilibrium thermodynamics, and particularly for the study of electron transport of any kind, such as the charge, heat and particle transport. Processes like those are also essential for the designing of any solid state device.

Nevertheless, all models of generation and recombination processes used today contradict fundamental physics such as those described by Maxwell's equations.

Most of the electron and hole transport phenomena usually are accompanied by appearance of nonequilibrium carriers of charge (see Ref. [1, 2, 3, 4, 5, 6, 7, 8]).

Their motion is described by the set of continuity equations for the electron \mathbf{j}_n , and hole \mathbf{j}_p current densities (Ref. [4, 8]),

$$\begin{aligned}\frac{\partial n}{\partial t} &= g_n + \frac{1}{e} \operatorname{div} \mathbf{j}_n - R_n, \\ \frac{\partial p}{\partial t} &= g_p - \frac{1}{e} \operatorname{div} \mathbf{j}_p - R_p,\end{aligned}\tag{1}$$

and by the Poisson equation (see Ref. [6, 8]),

$$\operatorname{div} \mathbf{E} = \frac{4\pi}{\varepsilon} \rho.\tag{2}$$

Here n and p are the total electron and hole concentrations, g_n and g_p are the electron and hole external generation rates, \mathbf{E} is the electric field, ρ is the bulk electric charge density, e is the hole charge, ε is the permittivity, R_n and R_p are the electron and hole recombination rates.

Usually, R_n and R_p are specified by the following equations (see Refs. [1, 2, 3, 4, 6, 8, 9]):

$$R_n = \frac{\delta n}{\tau_n}, \quad R_p = \frac{\delta p}{\tau_p},\tag{3}$$

where $\delta n = n - n_0$, $\delta p = p - p_0$, n_0 and p_0 are the equilibrium electron and hole concentrations; τ_n and τ_p are the electron and hole lifetimes.

Eqs. (3) are obtained for small deviations of the total concentrations from the equilibrium ones, $\delta n, \delta p \ll n_0, p_0$.

Subtracting the second equation from the first one [see Eqs.(1)], we obtain that

$$e(g_n - g_p) + \operatorname{div}(\mathbf{j}_n + \mathbf{j}_p) - e(R_n - R_p) = e \frac{\partial}{\partial t} (n - p).\tag{4}$$

At the same time, it is easy to obtain the continuity equation for the total current $\mathbf{j} = \mathbf{j}_n + \mathbf{j}_p$ from the Maxwell's equations,

$$\operatorname{div} \mathbf{j} = e \frac{\partial}{\partial t} (n - p + n_t), \quad (5)$$

where n_t is the concentration of captured electrons.

Comparing Eqs. (4) and (5) we get that

$$g_n - g_p = R_n - R_p - \frac{\partial n_t}{\partial t}. \quad (6)$$

After substituting Eq. (3) into Eq. (6) we will obtain an unphysical result. In this case we have one more correlation between δn and δp that overdetermines the set of Eqs. (1)-(2). The latter proves the incorrectness of Eqs. (3). It is interesting to note, as it follows from Eq. (6), in general case the rates R_n and R_p as functions of n and p are dependent on the external generation rates g_n and g_p .

At the same time, starting from the well known equation for the band-band recombination (see Ref. [2]),

$$R = \alpha(np - n_i^2), \quad (7)$$

it is easy to obtain that Eq. (6) will be satisfied identically. In Eq. (7) $n_i^2 = n_0 p_0$, n_i is the electron concentration in intrinsic semiconductor at the equilibrium temperature T_0 and α is the capture coefficient.

Actually, $g_n = g_p$, and $R_n = R_p$ if the impurity levels (traps) do not take part in the generation and recombination processes ($n_t = \text{const}$). From the above, instead Eq. (3), the equation for the band-band recombination must be

$$R_n = R_p = R = \frac{\delta n}{\tau_n} + \frac{\delta p}{\tau_p}. \quad (8)$$

Here $\tau_n = (\alpha p_0)^{-1}$, and $\tau_p = (\alpha n_0)^{-1}$. As usually, we have assumed that $\delta n, \delta p \ll n_0, p_0$.

It is necessary to emphasize that even if parameters τ_n and τ_p have dimension of time they are not the lifetimes of the nonequilibrium carriers. That follows straightforwardly from Eq. (1) after taking into account Eq. (8).

The lifetime of the charge carriers can be introduced only if $\delta n = \delta p$. The latter equality takes place if and only if all characteristic lengths of physical processes are much large than the Debye radius (the quasineutrality condition, see Ref. [6]). Moreover, the Maxwell's time

of the carriers have to be much less than the transition times and other characteristic times (see Ref. [6, 10]).

If $\delta n = \delta p$, then the lifetime for electrons as well as for holes will be given by one unique expression: $\tau = \tau_n \tau_p / (\tau_n + \tau_p)$.

Let us note that even in the case of intrinsic semiconductors ($n_0 = p_0$, $\tau_n = \tau_p$), the band-band recombination does not provide that $\delta n = \delta p$, contrary to widely spread opinion (see for instance Refs. [2, 3, 6, 8, 9, 10, 11]. Actually, the presence of terms $\text{div } \mathbf{j}_n$ and $\text{div } \mathbf{j}_p$ in Eq. (1), in general makes impossible the equality $\delta n = \delta p$.

As a rule, the electric current flowing through the semiconductor structure heats this structure. In this case the temperature of a sample becomes a function of the coordinates $T(\mathbf{r})$, see Refs. [2, 8, 10]. In some cases (thermoelectric phenomena, and devices based on these effects) the inhomogeneous temperature is created willingly, with the help of external heaters and coolers (Ref. [7]), or by heating with light (photothermal phenomena, see Ref. [12]).

Not only in this case but more generally the electron T_n , hole T_p and phonon T_{ph} temperatures are different [$T_n(\mathbf{r}) \neq T_p(\mathbf{r}) \neq T_{ph}(\mathbf{r})$], see Refs. [5, 8]. For simplicity, let us restrict ourselves to the case where the hole and the phonon temperatures are equal: [$T(\mathbf{r}) = T_p(\mathbf{r}) = T_{ph}(\mathbf{r})$]. At the same time we assume that the electron temperature $T_n(\mathbf{r})$ differs from the phonon temperature $T(\mathbf{r})$. Now, as it was shown in Refs. [13, 14], we can obtain that

$$R = \alpha[T_n(\mathbf{r}), T(\mathbf{r})]np - \alpha[T(\mathbf{r}), T(\mathbf{r})]n_i^2. \quad (9)$$

The first term in Eq. (9) corresponds to the capture of the charge carriers, and it depends on both temperatures. The second term corresponding to the thermal generation depends only on the phonon temperature $T(\mathbf{r})$.

Let us now suppose the temperatures $T_n(\mathbf{r})$ and $T(\mathbf{r})$ are to be small differed from the equilibrium temperature T_0 , i.e.,

$$T_n(\mathbf{r}) = T_0 + \delta T_n(\mathbf{r}), \quad T(\mathbf{r}) = T_0 + \delta T(\mathbf{r}), \quad \delta T_n, \quad \delta T \ll T_0.$$

Under this assumption we can get from Eq. (9) that the recombination rate

$$R = \frac{1}{\tau} \left[\frac{p_0}{n_0 + p_0} \delta n + \frac{n_0}{n_0 + p_0} \delta p - \beta \delta T + \gamma (\delta T_n - \delta T) \right]. \quad (10)$$

Here $\beta = \frac{n_0 p_0}{n_0 + p_0} \frac{1}{T_0} (3 + \frac{\varepsilon_g}{T_0})$, $\gamma = \frac{1}{\alpha} \frac{\partial \alpha}{\partial T_n} \Big|_{T_n=T_0} \frac{n_0 p_0}{n_0 + p_0}$, ε_g is the energy gap. Let us note that in this paper we use the energy system of units. From Eq. (10) it is easy to see that, even if $\delta n = \delta p$, the lifetime can not be introduced.

Situation becomes even more complicated if recombination resulting through the impurity centers (traps) is taken into account. Within the framework of the Shockley-Read model and with the assumption that the carriers of impurity centers are characterized by the temperature $T(\mathbf{r})$, the recombination can be given by the following equations, see Refs. [1, 2, 6, 10, 11]:

$$\begin{aligned} R_n &= \alpha_n(T_n, T)n(N_t - n_t) - \alpha_n(T, T)n_1 n_t, \\ R_p &= \alpha_p(T)p n_t - \alpha_p(T)p_1(N_t - n_t). \end{aligned} \tag{11}$$

Here N_t is the impurity concentration, α_n and α_p are the electron and hole capture coefficients, $n_1 = \nu_n(T)e^{-\varepsilon_t/T}$, $p_1 = \nu_p(T)e^{\frac{\varepsilon_t - \varepsilon_g}{T}}$, ε_t is the impurity energy level, $\nu_n(T) = \frac{1}{4} \left(\frac{2m_n T}{\pi \hbar^2} \right)^{\frac{3}{2}}$, $\nu_p(T) = \frac{1}{4} \left(\frac{2m_p T}{\pi \hbar^2} \right)^{\frac{3}{2}}$, and m_n and m_p are the electron and hole effective masses. As it follows from Eqs. (11), one more unknown value n_t arises when the recombination takes place through the impurity centers. Eq. (6) can be used just for its determination. Determining n_t from Eq. (6), and inserting it in Eq. (11) we obtain the recombination equation depending on n and p .

Below, for simplicity we will assume that $g_n = g_p = 0$. These equalities take place if the nonequilibrium carriers are generated due to injection, see. Refs. [2, 3, 4, 11] or redistribution (Ref. [7]) in semiconductor sample. One more example where this condition is fulfilled is the surface generation of photo-carriers in the sample, see Refs. [6, 9, 10].

In this case Eq. (6) serving for determination n_t for steady-state ($\partial n_t / \partial t = 0$) reduces to

$$R_n = R_p. \tag{12}$$

Determining from this equation n_t and inserting it in Eq. (11) it is easy to make sure that Eq. (12) turns to identity.

Suggesting, as it is made above, the deviation of all values to be small and representing n_t in the form $n_t = n_t^0 + \delta n_t$, where n_t^0 is the equilibrium concentration of electrons located

on the impurity levels, we can obtain the recombination rate through the traps as follows,

$$\begin{aligned}
R_n = R_p = R = \frac{1}{\tau} \left\{ \frac{N_t - n_t^0}{n_0 + n_1^0} \delta n + \frac{n_t^0}{p_0 + p_1^0} \delta p \right. \\
- \frac{n_t^0}{n_0 + n_1^0} \delta n_1 - \frac{N_t - n_t^0}{p_0 + p_1^0} \delta p_1 \\
+ \frac{1}{\alpha_n} \frac{\partial \alpha_n}{\partial T_n} \Big|_{T_n=T_0} \frac{n_0(N_t - n_t^0)}{p_0 + p_1^0} (\delta T_e - \delta T) \\
+ \left[\frac{1}{\alpha_n} \left(\frac{\partial \alpha_n}{\partial T_n} \Big|_{T_n=T_0} + \frac{\partial \alpha_n}{\partial T} \Big|_{T=T_0} \right) \frac{n_0(N_t - n_t^0) - n_1^0 n_t^0}{n_0 + n_1^0} \right. \\
\left. - \frac{1}{\alpha_p} \frac{\partial \alpha_p}{\partial T} \Big|_{T=T_0} \frac{p_1^0(N_t - n_t^0) - p_0 n_t^0}{p_0 + p_1^0} \right] \delta T \left. \right\} \quad (13)
\end{aligned}$$

Here

$$\frac{1}{\tau} = \frac{\alpha_n(T_0, T_0) \alpha_p(T_0) (n_0 + n_1^0) (p_0 + p_1^0)}{\alpha_n(T_0, T_0) (n_0 + n_1^0) + \alpha_p(T_0) (p_0 + p_1^0)}.$$

Obtaining Eq. (13) we have taken into account that n_1 and p_1 can be presented in the following form, $n_1 = n_1^0 + \delta n_1$, $p_1 = p_1^0 + \delta p_1$. Here $\delta n_1 = \frac{n_1^0}{T_0} \left(\frac{3}{2} + \frac{\varepsilon_t}{T_0} \right) \delta T$ and $\delta p_1 = \frac{p_1^0}{T_0} \left(\frac{3}{2} - \frac{\varepsilon_t - \varepsilon_g}{T_0} \right) \delta T$.

Let us note that the concentrations of nonequilibrium carriers δn and δp turn to zero at the strong recombination ($\tau \rightarrow 0$) if only $\delta T = \delta T_n = 0$, as it follows from Eqs. (8), (10), and (13). As a matter of fact, since R is always the finite value, the expression in braces (13) must vanish with $\tau \rightarrow 0$. This implies that equality $\delta n = \delta p = 0$ takes place only if $\delta T_n = \delta T = 0$, [see for example Eq. (8)].

Summarizing, in this Communication we have shown that for the depiction of generation and recombination phenomena to be consistent with Maxwell's equations, essential modifications are required. According with our results, it is necessary to replace the standard expressions for recombination involving lifetimes for nonequilibrium electrons and holes with expressions obtained when the definition of lifetime lost physical sense.

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